AUTOMOTIVE

Rohs

**HALOGEN** 

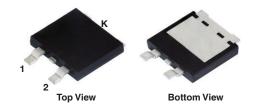
FREE

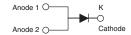


## Vishay Semiconductors

# Hyperfast Rectifier, 16 A FRED Pt®

### eSMP<sup>®</sup> Series SMPD (TO-263AC)





#### **LINKS TO ADDITIONAL RESOURCES**



PRIMARY CHARACTERISTICS				
I <sub>F(AV)</sub>	16 A			
$V_{R}$	600 V			
V <sub>F</sub> at I <sub>F</sub> (T <sub>J</sub> = 150 °C)	1.24 V			
t <sub>rr</sub>	30 ns			
T <sub>J</sub> max.	175 °C			
Package	SMPD (TO-263AC)			
Circuit configuration	Single			

#### **FEATURES**

Hyperfast recovery time, reduced Q<sub>rr</sub>, and soft recovery



- For PFC CRM, snubber operation
- Low forward voltage drop
- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 qualified, meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>

#### **DESCRIPTION / APPLICATIONS**

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop and ultrafast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in PFC, boost, lighting, in the AC/DC section of SMPS, freewheeling and clamp diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element and snubbers.

#### **MECHANICAL DATA**

Case: SMPD (TO-263AC)

Molding compound meets UL 94 V-0 flammability rating

Halogen-free, RoHS-compliant

Terminals: matte tin plated leads, solderable per

J-STD-002

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Peak repetitive reverse voltage	$V_{RRM}$		600	V
Average rectified forward current	I <sub>F(AV)</sub> (1)	T <sub>C</sub> = 127 °C	16	٨
Non-repetitive peak surge current	I <sub>FSM</sub>	T <sub>J</sub> = 25 °C, 10 ms sine pulse	160	Α .

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	$V_{BR}$ , $V_{R}$	I <sub>R</sub> = 100 μA	600	-	-	
Compared violations	alta a a	I <sub>F</sub> = 16 A	-	1.65	2.15	V
Forward voltage	$V_{F}$	I <sub>F</sub> = 16 A, T <sub>J</sub> = 150 °C	-	1.24	1.65	
Dayaraa laakaaa ayrraat		V <sub>R</sub> = V <sub>R</sub> rated	-	-	20	
Reverse leakage current I <sub>R</sub>	I <sub>R</sub>	T <sub>J</sub> = 150 °C, V <sub>R</sub> = V <sub>R</sub> rated	-	-	500	μΑ
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 600 V	-	16	-	pF

#### Note

(1) Mounted on infinite heatsink



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<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CON	TEST CONDITIONS		TYP.	MAX.	UNITS
		$I_F = 1 A, dI_F/dt = 50$	A/μs, V <sub>R</sub> = 30 V	-	30	1	
Reverse recovery time	+	$I_F = 0.5 \text{ A}, I_R = 1 \text{ A}, I_{rr} = 0.25 \text{ A}$		-	-	30	]
neverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	43	-	ns
		T <sub>J</sub> = 125 °C		-	92	-	
Peak recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 25 °C	l <sub>F</sub> = 16 A, dl <sub>F</sub> /dt = 500 A/μs,	-	7.7	-	Α
Feak recovery current		T <sub>J</sub> = 125 °C	$V_{R} = 400 \text{ V}$	-	13.8	-	] ^
Poverse recovery charge	T <sub>J</sub> = 25 °C		-	150	1	μC	
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	600	-	μΟ

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55	-	+175	°C
Thermal resistance, junction to mount	R <sub>thJM</sub>		-	1.2	1.7	°C/W
Approximate weight				0.55		g
Marking device		Case style SMPD (TO-263AC)		16E	DH06	

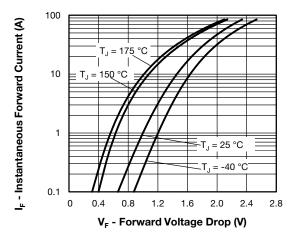


Fig. 1 - Typical Forward Voltage Drop Characteristics

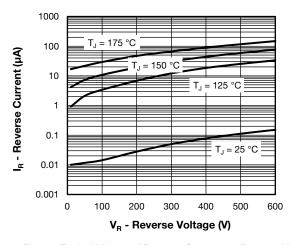


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

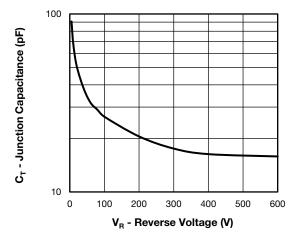


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage



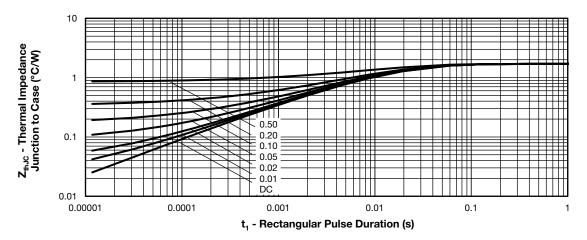


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics

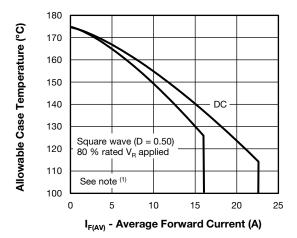


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

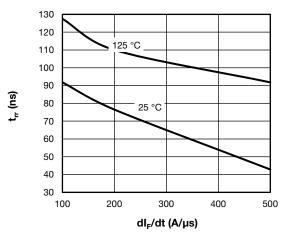


Fig. 6 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

#### Note

 $^{(1)}$  Formula used: T<sub>C</sub> = T<sub>J</sub> - (Pd + Pd<sub>REV</sub>) x R<sub>thJC</sub>; Pd = forward power loss = I<sub>F(AV)</sub> x V<sub>FM</sub> at (I<sub>F(AV)</sub>/D) (see fig. 5); Pd<sub>REV</sub> = inverse power loss = V<sub>R1</sub> x I<sub>R</sub> (1 - D); I<sub>R</sub> at V<sub>R1</sub> = rated V<sub>R</sub>

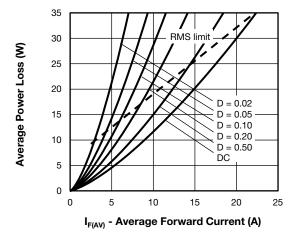


Fig. 7 - Forward Power Loss Characteristics

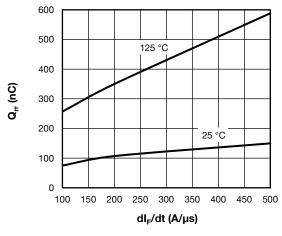
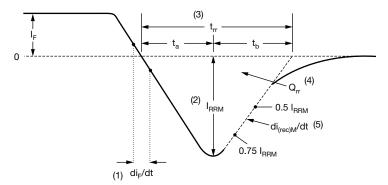


Fig. 8 - Typical Stored Charge vs. dl<sub>F</sub>/dt

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- (1) di<sub>F</sub>/dt rate of change of current through zero crossing
- (2)  $I_{RRM}$  peak reverse recovery current  $O_{-}=-$
- (3)  $\rm t_{rr}$  reverse recovery time measured from zero crossing point of negative going  $\rm I_{rr}$  to point where a line passing through 0.75  $\rm I_{RRM}$  and 0.50  $\rm I_{RRM}$  extrapolated to zero current.
- (4)  $\mathbf{Q}_{rr}$  area under curve defined by  $\mathbf{t}_{rr}$  and  $\mathbf{I}_{RRM}$

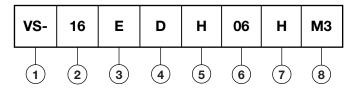
$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) di<sub>(rec)M</sub>/dt - peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

Fig. 9 - Reverse Recovery Waveform and Definitions

#### **ORDERING INFORMATION TABLE**

**Device code** 



- Vishay Semiconductors product
- 2 Current rating (16 A)
- Circuit configuration:

E = single die

- 4 D = SMPD package
- 5 Process type,

H = hyperfast recovery

- 6 Voltage code (06 = 600 V)
- 7 H = AEC-Q101 qualified
- 8 M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)					
PREFERRED P/N	QUANTITY PER REEL	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION		
VS-16EDH06HM3/I (1)	2000	2000	13" diameter plastic tape and reel		

### Note

(1) AEC-Q101 qualified

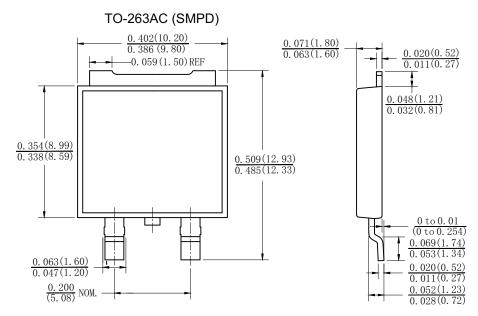
LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95604			
Part marking information	www.vishay.com/doc?95566			
Packaging information	www.vishay.com/doc?88869			



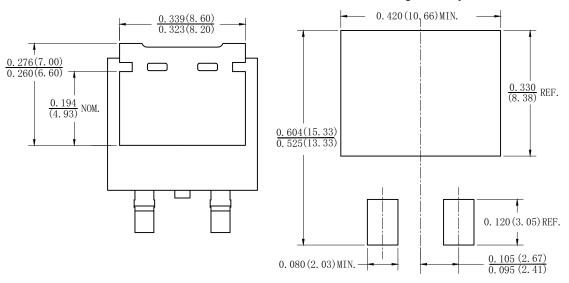
Vishay Semiconductors

# TO-263AC (SMPD)

### **DIMENSIONS** in inches (millimeters)



#### Mounting Pad Layout





## **Legal Disclaimer Notice**

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